



PATENT

Case Docket No. MICRON.129DV1C1

Date: March 26, 2004

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Ronald A. Weimer  
Appl. No. : 10/758,518  
Filed : January 15, 2004  
For : METHOD OF FABRICATING  
AN INTEGRATED CIRCUIT  
WITH DIELECTRIC LAYER  
EXPOSED TO A HYDROGEN-  
BEARING NITROGEN SOURCE  
Examiner : Unknown  
Group Art Unit : Unknown

I hereby certify that this correspondence and all marked attachments are being deposited with the United States Postal Service as first class mail in an envelope addressed to: Commissioner for Patents, P.O. Box 1450, Alexandria, VA 22313-1450, on

March 26, 2004

(Date)

Bruce S. Itchkawitz, Reg. No. 47,677

TRANSMITTAL LETTER

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

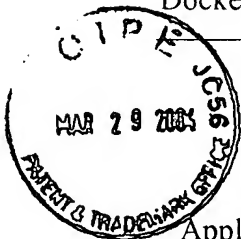
Dear Sir:

Enclosed for filing in the above-identified application are:

- (X) An Information Disclosure Statement.
- (X) A PTO Form 1449 listing sixty-eight (68) references.
- (X) A return prepaid postcard.

The Commissioner is hereby authorized to charge any additional fees which may be required, or credit any overpayment, to Account No. 11-1410.

Bruce S. Itchkawitz  
Registration No. 47,677  
Attorney of Record  
Customer No. 20,995  
(949) 760-0404



## INFORMATION DISCLOSURE STATEMENT

Applicant : Ronald A. Weimer  
App. No. : 10/758,518  
Filed : January 15, 2004  
For : METHOD OF FABRICATING AN  
INTEGRATED CIRCUIT WITH  
DIELECTRIC LAYER EXPOSED TO A  
HYDROGEN-BEARING NITROGEN  
SOURCE  
Examiner : Unknown  
Group Art Unit : Unknown

Commissioner for Patents  
P.O. Box 1450  
Alexandria, VA 22313-1450

Dear Sir:

Enclosed is form PTO-1449 listing sixty-eight (68) references that are of record in U.S. patent application No. 10/378,568, filed March 3, 2003, which is the parent of this continuation application, and is relied upon for an earlier filing date under 35 U.S.C. § 120. Copies of the references are not submitted pursuant to 37 C.F.R. § 1.98(d).

This Information Disclosure Statement is being filed before the receipt of a first Office Action on the merits, and presumably no fee is required in accordance with 37 C.F.R. § 1.97(b)(3). If a first Office Action on the merits was mailed before the mailing date of this Statement, the Commissioner is authorized to charge the fee set forth in 37 C.F.R. § 1.17(p) to Deposit Account No. 11-1410.

Respectfully submitted,

KNOBBE, MARTENS, OLSON & BEAR, LLP

Dated: 3/26/04

By: Bruce S. Itchkawitz

Bruce S. Itchkawitz  
Registration No. 47,677  
Attorney of Record  
Customer No. 20,995  
(949) 760-0404

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE SUPPLEMENTARY INFORMATION DISCLOSURE STATEMENT BY APPLICANT (USE SEVERAL SHEETS IF NECESSARY)	ATTY. DOCKET NO. MICRON.129DV1C1	APPLICATION NO. 10/758,518
	APPLICANT Ronald A. Weimer	
	FILING DATE January 15, 2004	GROUP Unknown

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	1	4,142,004	02/27/79	Hauser, Jr. et al.			
	2	4,551,231	11/05/85	Kovach et al.			
	3	4,623,912	11/18/86	Chang et al.			
	4	4,814,292	03/21/89	Sasaki et al.			
	5	4,872,043	10/03/89	Fujii			
	6	5,102,832	04/07/92	Tuttle			
	7	5,112,773	05/12/92	Tuttle			
	8	5,159,430	10/27/92	Manning et al.			
	9	5,288,527	02/22/94	Jousse et al.			
	10	5,352,330	10/04/94	Wallace			
	11	5,366,917	11/22/94	Watanabe et al.			
	12	5,385,863	01/31/95	Tatsumi			
	13	5,397,720	03/14/95	Kwong et al.			
	14	5,445,999	08/29/95	Thakur et al.			
	15	5,489,542	02/06/96	Iwai et al.			
	16	5,707,746	01/13/98	Yaoi et al.			
	17	5,707,898	01/13/98	Keller et al.			
	18	5,711,998	01/27/98	Shufflebotham			
	19	5,821,603	10/13/98	Puntambekar			
	20	5,880,008	03/09/99	Akiyama et al.			
	21	5,904,860	05/18/99	Nagakubo et al.			
	22	5,936,291	08/31/99	Makita et al.			
	23	5,946,542	08/31/99	Iyer			
	24	5,972,765	10/26/99	Clark et al.			
	25	5,972,804	10/26/99	Tobin et al.			
	26	6,013,310	01/11/00	Yaoi et al.			
	27	6,017,784	01/25/00	Ohta et al.			
	28	6,017,808	01/25/00	Wang et al.			

EXAMINER

DATE CONSIDERED

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED. INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FORM PTO-1449	U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.129DV1C1	APPLICATION NO. 10/758,518
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)		APPLICANT Ronald A. Weimer	
		FILING DATE January 15, 2004	GROUP Unknown

## U.S. PATENT DOCUMENTS

EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUBCLASS	FILING DATE (IF APPROPRIATE)
	29	6,025,281	02/15/00	Passlack et al.			
	30	6,048,795	04/11/00	Numasawa et al.			
	31	6,087,206	07/11/00	Hamada, Koji			
	32	6,136,641	10/24/00	Won et al.			
	33	6,143,608	11/07/00	He et al.			
	34	6,147,014	11/14/00	Lyding et al.			
	35	6,150,725	11/21/00	Misawa et al.			
	36	6,197,701 B1	03/06/01	Shue et al.			
	37	6,204,203 B1	03/20/01	Narwankar et al.			
	38	6,248,673 B1	06/19/01	Huang et al.			
	39	6,251,726 B1	06/26/01	Huang			
	40	6,255,230 B1	07/24/01	Ikakura et al.			
	41	6,258,730 B1	07/03/01	Sun et al.			
	42	6,265,327 B1	07/10/01	Kobayashi et al.			
	43	6,274,442 B1	08/14/01	Gardner et al.			
	44	6,284,583 B1	09/04/01	Saida et al.			
	45	6,316,354 B1	11/13/01	Hu			
	46	6,323,519 B1	11/27/01	Gardner et al.			
	47	6,348,380 B1	02/19/02	Weimer et al.			
	48	6,380,014 B1	04/30/02	Ohta et al.			
	49	6,387,761 B1	05/14/02	Shih et al.			
	50	6,420,752 B1	07/16/02	Ngo et al.			
	51	6,465,370 B1	10/15/02	Schrems et al.			
	52	6,483,172 B1	11/19/02	Cote et al.			
	53	6,485,988 B2	11/26/02	Ma et al.			
	54	6,544,908 B1	04/08/03	Weimer et al.			
	55	6,551,867 B1	04/22/03	Ozeki et al.			
	56	6,559,007 B1	05/06/03	Weimer			

EXAMINER

DATE CONSIDERED

\*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.

FORM PTO-1449 U.S. DEPARTMENT OF COMMERCE PATENT AND TRADEMARK OFFICE	ATTY. DOCKET NO. MICRON.129DV1C1	APPLICATION NO. 10/758,518
SUPPLEMENTAL INFORMATION DISCLOSURE STATEMENT BY APPLICANT  (USE SEVERAL SHEETS IF NECESSARY)	APPLICANT Ronald A. Weimer	
	FILING DATE January 15, 2004	GROUP Unknown

FOREIGN PATENT DOCUMENTS								
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUBCLASS	TRANSLATION	
							YES	NO

EXAMINER INITIAL	OTHER DOCUMENTS (INCLUDING AUTHOR, TITLE, DATE, PERTINENT PAGES, ETC.)	
	57	Cheng et al., Effects of NH <sub>3</sub> Plasma Passivation on N-Channel Polycrystalline Silicon Thin-Film Transistors, IEEE, Vol. 44, No. 1, pp. 64-68, January 1997.
	58	U.S. Patent Application No. 10/377,495 entitled "AMMONIA GAS PASSIVATION ON NITRIDE ENCAPSULATED DEVICES" in 28 pages with 5 sheets of drawings.
	59	U.S. Patent Application No. 10/012,665 entitled "AMMONIA GAS PASSIVATION ON NITRIDE ENCAPSULATED DEVICES" in 21 pages with 5 sheets of drawings.
	60	Intel Corporation, <i>Intel StratFlash™ Memory Development and Implementation</i> , <a href="http://www.chips.com/technology/itj/q41997/articles/art_2b.htm">http://www.chips.com/technology/itj/q41997/articles/art_2b.htm</a> , December 9, 1999; pp. 1-5.
	61	Chevalier, <i>Electroless Gold Plating</i> , Plating and Electroplating, pp. 323-325.
	62	Lifshitz et al., <i>Detection of water-related charge in electronic dielectrics</i> , Appl. Phys. Lett. Vol. 55, Issue 4, July 24, 1989, pp. 408-410.
	63	Momose et al., <i>Very Lightly Nitrided Oxide Gate Mosfets For Deep-sub-micron CMOS Devices</i> , IEDM, 1991, pp. 359-362.
	64	Vanheusden et al., <i>Positive charging of buried SiO<sub>2</sub> by hydrogenation</i> , Appl. Phys. Lett., Vol. 64, No. 19, May 9, 1994, pp. 2575-2577.
	65	Vines et al., <i>Platinum Metals</i> , Chapter 13 of Characteristics of the Platinum Metals, pp. 342-356.
	66	Sakai et al., <i>Novel seeding method for the growth of polycrystalline Si films with hemispherical grains</i> , Appl. Phys. Lett., Vol. 61, No. 2, July 13, 1992, pp. 159-161.
	67	<i>Superconducting RF Cavities: A Primer</i> , Basics of SRF Cavities 3.1: Fowler-Nordheim Theory, <a href="http://www.lns.cornell.edu/upblic/CESR/SRF/BasicSRF/SRFBas31.html">http://www.lns.cornell.edu/upblic/CESR/SRF/BasicSRF/SRFBas31.html</a> , December 9, 1999.
	68	Watanabe et al., <i>Hemispherical Grained Si Formation on in-situ Phosphorous Doped Amorphous-Si Electrode for 256Mb DRAM's Capacitor</i> , IEEE Transactions on Electron Devices, Vol. 42, No. 7, July 1995, pp. 1247-1254.

H:\DOCS\BS\BSI-5407.DOC  
032604

EXAMINER	DATE CONSIDERED
*EXAMINER: INITIAL IF CITATION CONSIDERED, WHETHER OR NOT CITATION IS IN CONFORMANCE WITH MPEP 609; DRAW LINE THROUGH CITATION IF NOT IN CONFORMANCE AND NOT CONSIDERED, INCLUDE COPY OF THIS FORM WITH NEXT COMMUNICATION TO APPLICANT.	